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# On the pairing mechanism of unconventional high temperature superconductor materials

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## <u>Acknowledgements</u>

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Material View: High-Temperature Superconductivity

> Layered structure (Bi<sub>2</sub>Sr<sub>2</sub>CaCu<sub>2</sub>O<sub>8+δ</sub>)

NON-SC	BiO/SrO	非超导层
SC	CuO <sub>2</sub>	超导层
NON-SC	BiO/SrO	非超导层
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NON-SC	BiO/SrO	非超导层

## The most unconventional aspect of HTS

- **1.** Complex layered structure
- 2. Carrier density in CuO<sub>2</sub> (FeAs/FeSe)





#### **Bi-2212**

BiOterminated surface

## The most unconventional aspect of HTS

## Complex layered structure Carrier density in CuO<sub>2</sub> (FeAs/FeSe)



## **STM/STS of FeSe on STO**

Q. Y. Wang et al., Chin. Phys. Lett. 29, 037402 (2012)



## Monolayer FeSe on STO: Tc ~ 65 K - 100 K

My group: Chin. Phys. Lett. 29, 037402 (2012)



## Gap Symmetry & Tc by ARPES: Isotropic



#### **Plain s-wave pairing + electron-phonon coupling**





FFT (B=0)



Z. X. Shen & D. H. Lee Nature 515, 245 (2014)



Jimin Zhao PRL 116, 107001 (2016)

T. Zhang & D. L. Feng Nature Physics 11, 946 (2015)

### **Ozone-assisted MBE growth of CuO<sub>2</sub> films on Bi-2212**





Zhong and Wang et al., Sci. Bull. 61, 1239 (2016)



Ji et al., PRL 100, 226801 (2008)

## Bi-2212 surface: UHV cleaving CuO<sub>2</sub> growth: Cu: 99.9% Ozone flux: $1.0 \sim 5.0 \times 10^{-5}$ Torr

## MBE growth of $CuO_2$ films on $Bi_2Sr_2CaCu_2O_{8+\delta}$

CuO<sub>2</sub> •••••• •O •Sr •Cu •Ca •Bi

The same to the bulk



## **Two important results from 1UC CuO<sub>2</sub> films**



(1) No change in the Mott-Hubbard band structure of  $CuO_2$  (regardless of the doping).

(2) U-shaped gap on  $CuO_2$ , not the V-gap on the cleaved BiO surface.

The assumption that the "V" gap is tunneling from the underlying  $CuO_2$  is NOT correct.



#### **Cuprates: interface enhanced BCS superconductor?**

### **Robust U-Gap of Monolayer CuO<sub>2</sub> on Bi-2212 (raw data)**



Red background: normal-state fit The normal state: particle-hole symmetry (Fermi-liquid behavior) Red background: normal-state fit The normal state: particle-hole asymmetry (doped Mott insulator)

Zhong et al., unpublished data (2017)

#### **Robust U-Gap of Monolayer CuO<sub>2</sub> on Bi-2212**



Zhong et al., unpublished data (2017)

## STS spectra of the cleaved CuO<sub>2</sub> surface of BSCCO

Yazdani Group: PRL 89, 087002(2002)



## Our original proposal for raising $T_c$ (2008)

**BCS**  
Theory
$$T_{c} = \frac{w_{0}}{1.2} \exp\left[-\frac{1.04(1+\lambda)}{\lambda - \mu^{*}(1+0.62\lambda)}\right] \qquad w_{o} \sim 300 \text{ K}$$

W. L. McMillan, Phys. Rev. B16, 643 (1977)

Metal: conducting, but low Debye  $W_o$ 

Ceramic (diamond): high Debye  $W_0$ , but insulating. (Heavy doping destroys phase coherence)

#### To raise Tc under BCS e-ph coupling scheme

"soft" conductor + "hard" reservoir: heterostructure of two materials may overcome the Tc limit for one material



## High Tc by doping of a parent insulator

Conduction

Band (Ec)



## High mobility 2DEG in modulation-doped semiconductor heterostructures Dingle

Dingle, Störmer, Gossard, Wiegmann, APL **33**, 665 (1978)



- (1) Charge transfer  $\rightarrow$  Band bending  $\rightarrow$  QW (2DEG).
- (2) Without QW formation in its interface side, the GaAs cannot conduct !!!
- (3) Spatially separated electrons and their parent atoms.

## **Our Model: 2D Hole Liquid (2DHL)**



### **Band bending occurs at Mott-insulator/STO heterostructure**



## **BCS superconductors**

 $T_{C} \sim 40 \text{ K}$  (low  $w_{o}$  and limited  $\lambda$ )

conventional

T<sub>C</sub> > 77 KInterface Enhancementat heterostructures

unconventional

Thank you very much!